

Silicon NPN Power Transistors

2N6326 2N6327 2N6328

DESCRIPTION

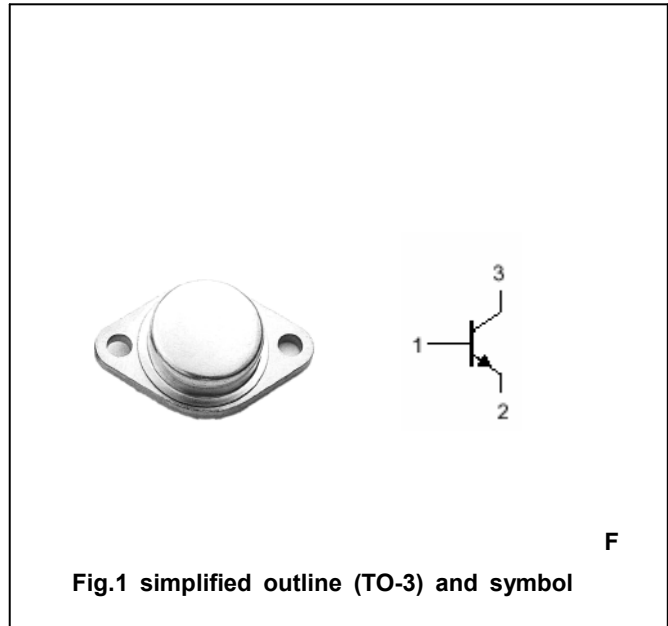
- With TO-3 package
- Low collector saturation voltage
- High DC current gain

APPLICATIONS

- Designed for audio amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6326	60	V
		2N6327	80	
		2N6328	100	
V_{CEO}	Collector-emitter voltage	2N6326	60	V
		2N6327	80	
		2N6328	100	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		30	A
I_B	Base current		7.5	A
P_D	Total power dissipation	$T_C = 25 \square$	200	W
T_j	Junction temperature		200	\square
T_{stg}	Storage temperature		-65~200	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	0.875	\square/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6326	I _C =0.2 A ; I _B =0			V
		2N6327				
		2N6328				
V _{CEsat}	Collector-emitter saturation voltage	I _C =15A; I _B =1.5A			1.2	V
V _{BEsat}	Base-emitter saturation voltage	I _C =15A; I _B =1.5A			1.5	V
V _{BE}	Base-emitter on voltage	I _C =8A ; V _{CE} =4V			1.5	V
I _{CBO}	Collector cut-off current	2N6326				mA
		2N6327				
		2N6328				
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	I _C =8A ; V _{CE} =4V	25			
h _{FE-2}	DC current gain	I _C =30A ; V _{CE} =4V	6		30	
f _T	Transition frequency	I _C =1A ; V _{CE} =10V;f=1.0MHz	3			MHz

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PACKAGE OUTLINE

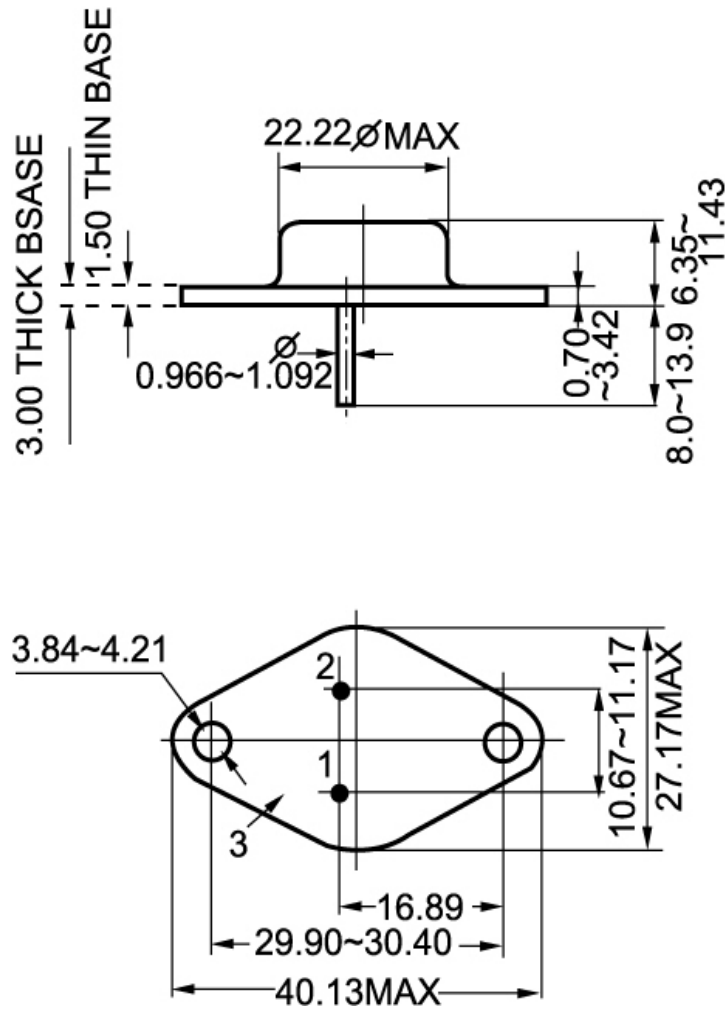


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)